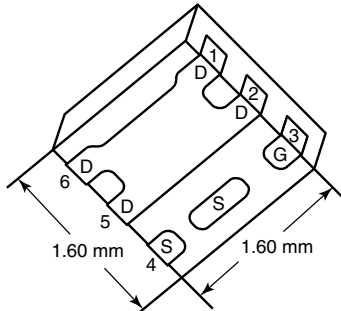


P-Channel 1.2 V (G-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω) Max.	I _D (A) ^g	Q _g (Typ.)
- 8	0.032 at V _{GS} = - 4.5 V	- 9 ^a	11.3 nC
	0.045 at V _{GS} = - 2.5 V	- 9 ^a	
	0.063 at V _{GS} = - 1.8 V	- 9 ^a	
	0.120 at V _{GS} = - 1.5 V	- 8.8	
	0.230 at V _{GS} = - 1.2 V	- 6.4	

PowerPAK SC-75-6L-Single


Ordering Information:
SiB417AEDK-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

- TrenchFET[®] Power MOSFET
- Thermally Enhanced PowerPAK[®] SC-75 Package
 - Small Footprint Area
 - Low On-Resistance
- 100 % R_g Tested
- Typical ESD Protection 2500 V
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

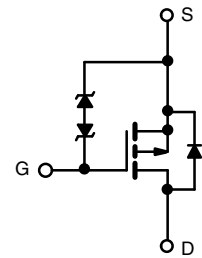
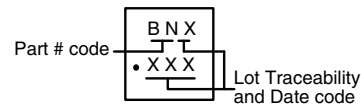


RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Load Switch for Portable Devices, Smart Phones, and Tablet PCs
 - Low Voltage Drop
 - Space Savings

Marking Code



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	- 8	V
Gate-Source Voltage	V _{GS}	± 5	
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	- 9 ^a
		T _C = 70 °C	- 9 ^a
		T _A = 25 °C	- 7.2 ^{b, c}
		T _A = 70 °C	- 5.7 ^{b, c}
Pulsed Drain Current (t = 300 μs)	I _{DM}	- 15	A
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	
		T _A = 25 °C	- 2 ^{b, c}
Maximum Power Dissipation	P _D	T _C = 25 °C	13
		T _C = 70 °C	8.4
		T _A = 25 °C	2.4 ^{b, c}
		T _A = 70 °C	1.6 ^{b, c}
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C
Soldering Recommendations (Peak Temperature) ^{d, e}		260	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{b, f}	R _{thJA}	41	51	°C/W	
Maximum Junction-to-Case (Drain)	R _{thJC}	7.5	9.5		

Notes:

- Package limited.
- Surface mounted on 1" x 1" FR4 board.
- t = 5 s.
- See solder profile (www.vishay.com/doc?73257). The PowerPAK SC-75 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- Maximum under steady state conditions is 105 °C/W.
- Based on T_C = 25 °C.

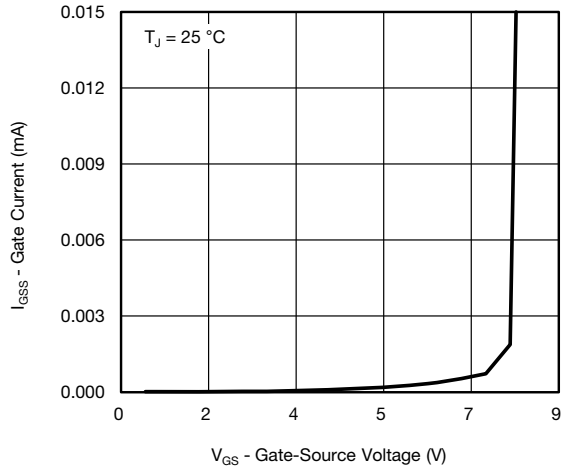
SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	- 8			V	
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = -250\text{ }\mu\text{A}$		- 6.1		mV/°C	
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			2.1			
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	- 0.35		- 1	V	
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 5\text{ V}$			± 20	μA	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -8\text{ V}, V_{GS} = 0\text{ V}$ $V_{DS} = -8\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			- 1 - 10		
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \leq -5\text{ V}, V_{GS} = -4.5\text{ V}$	- 15			A	
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -4.5\text{ V}, I_D = -3\text{ A}$		0.0265	0.0320	Ω	
		$V_{GS} = -2.5\text{ V}, I_D = -3\text{ A}$		0.0360	0.0450		
		$V_{GS} = -1.8\text{ V}, I_D = -1\text{ A}$		0.0500	0.0630		
		$V_{GS} = -1.5\text{ V}, I_D = -0.5\text{ A}$		0.0600	0.1200		
		$V_{GS} = -1.2\text{ V}, I_D = -0.5\text{ A}$		0.1000	0.2300		
Forward Transconductance ^a	g_{fs}	$V_{DS} = -4\text{ V}, I_D = -7.4\text{ A}$		18		S	
Dynamic^b							
Input Capacitance	C_{iss}	$V_{DS} = -4\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		878		pF	
Output Capacitance	C_{oss}			415			
Reverse Transfer Capacitance	C_{rss}			735			
Total Gate Charge	Q_g	$V_{DS} = -4\text{ V}, V_{GS} = -5\text{ V}, I_D = -7.4\text{ A}$		12.3	18.5	nC	
Gate-Source Charge	Q_{gs}	$V_{DS} = -4\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -7.4\text{ A}$		11.3	17		
Gate-Drain Charge	Q_{gd}			1.35			
Gate Resistance	R_g			3.42			
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -4\text{ V}, R_L = 0.68\text{ }\Omega$ $I_D \cong -5.9\text{ A}, V_{GEN} = -4.5\text{ V}, R_g = 1\text{ }\Omega$		1.3	6.5	13	Ω
Rise Time	t_r				19	29	ns
Turn-Off Delay Time	$t_{d(off)}$				18	27	
Fall Time	t_f				32	48	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$			- 9	A	
Pulse Diode Forward Current	I_{SM}				- 15		
Body Diode Voltage	V_{SD}	$I_S = -5.9\text{ A}, V_{GS} = 0\text{ V}$		- 0.8	- 1.2	V	
Body Diode Reverse Recovery Time	t_{rr}	$I_F = -5.9\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		32	48	ns	
Body Diode Reverse Recovery Charge	Q_{rr}			13	20	nC	
Reverse Recovery Fall Time	t_a			14		ns	
Reverse Recovery Rise Time	t_b			18			

Notes:

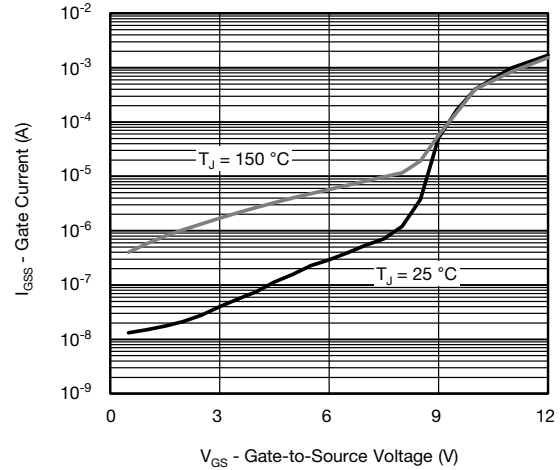
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

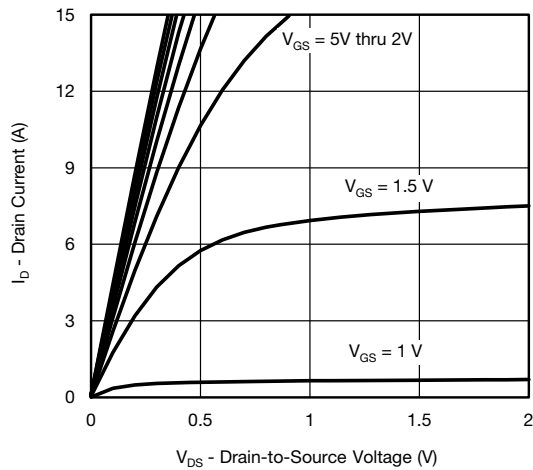
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



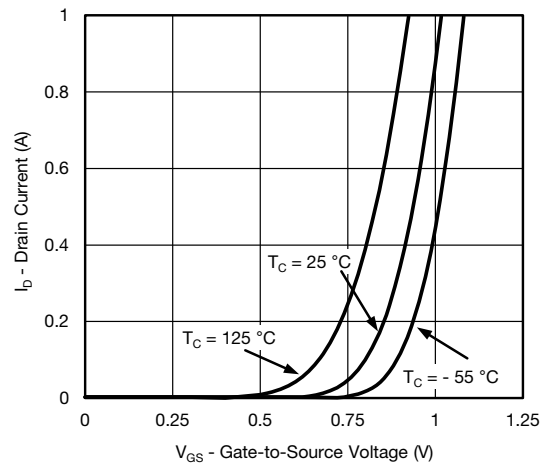
Gate Source Voltage vs. Gate Current



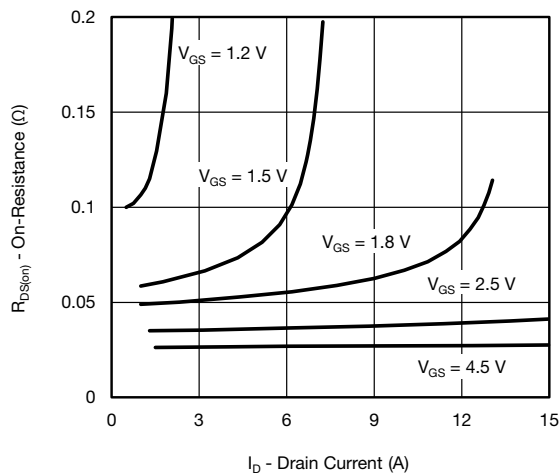
Gate Source Voltage vs. Gate Current



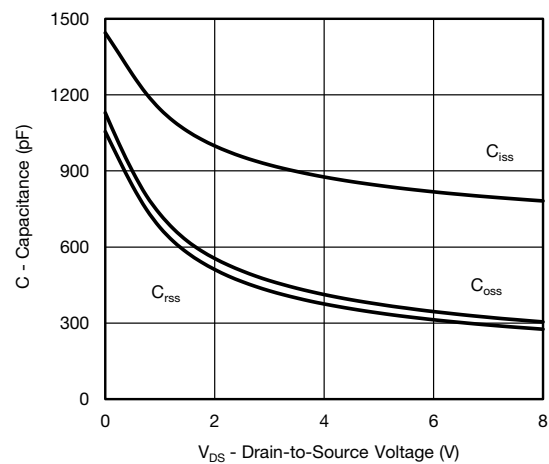
Output Characteristics



Transfer Characteristics

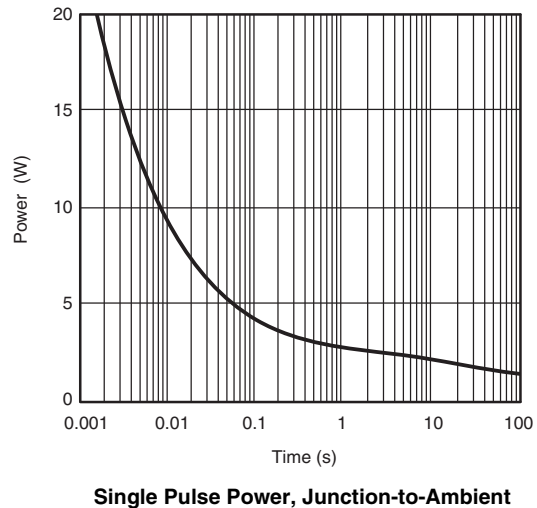
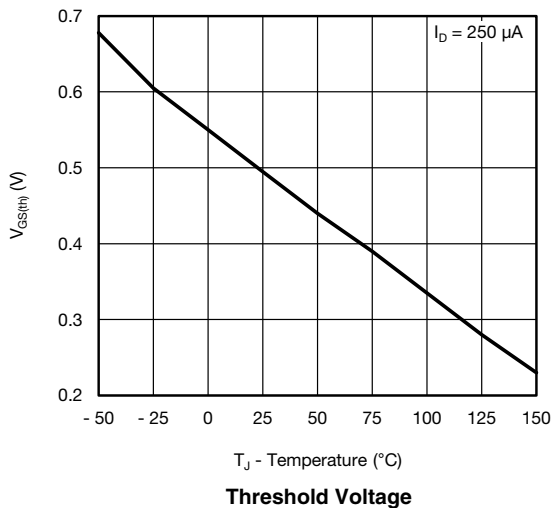
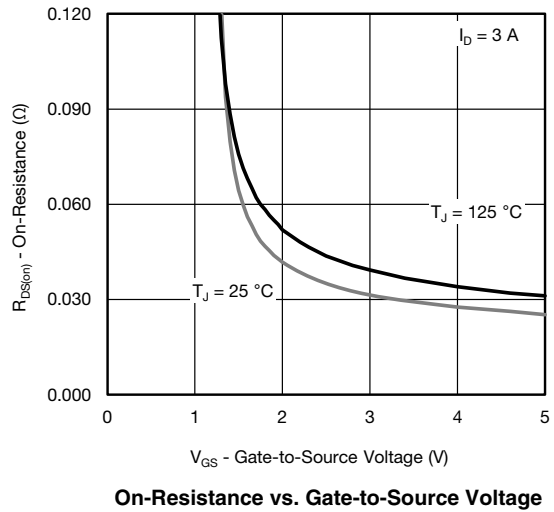
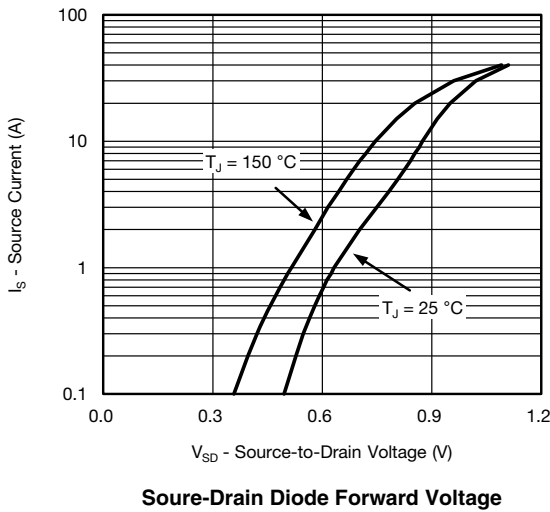
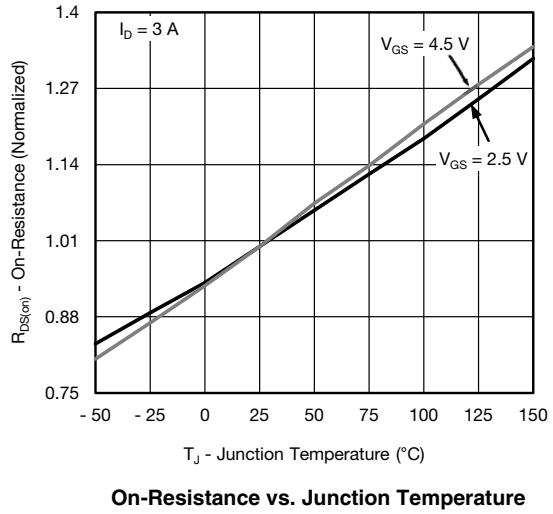
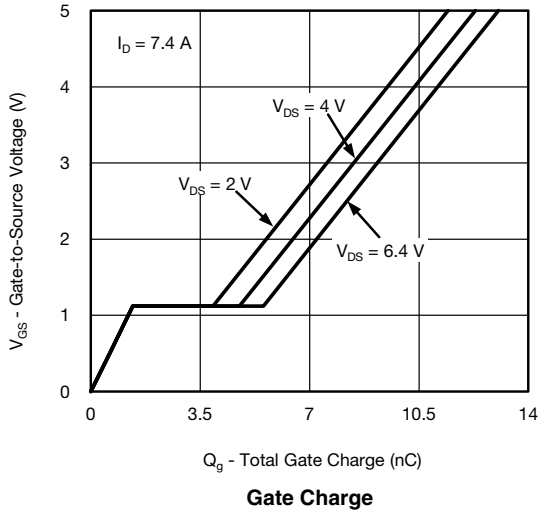


On-Resistance vs. Drain Current and Gate Voltage

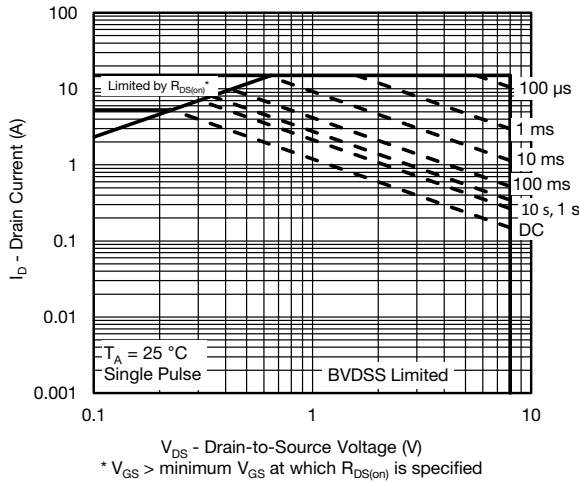


Capacitance

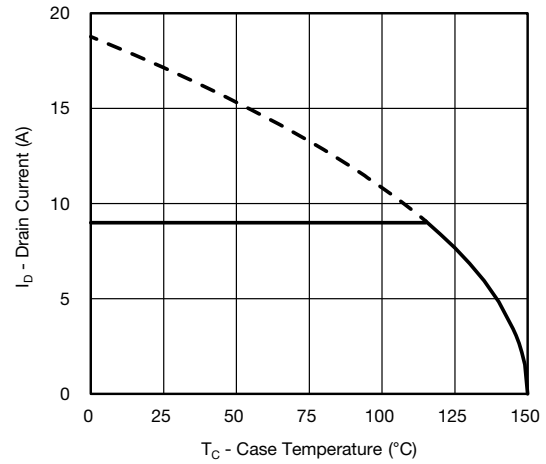
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



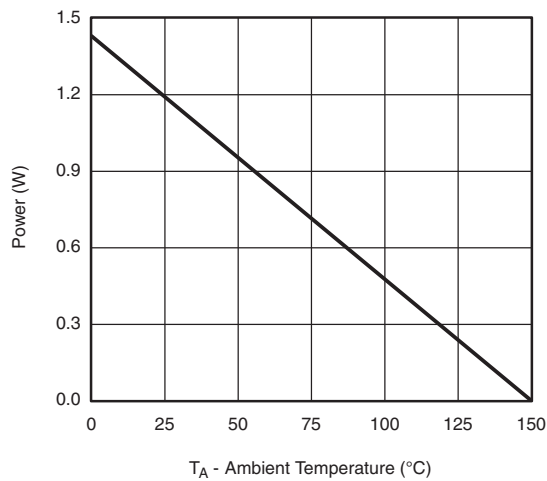
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



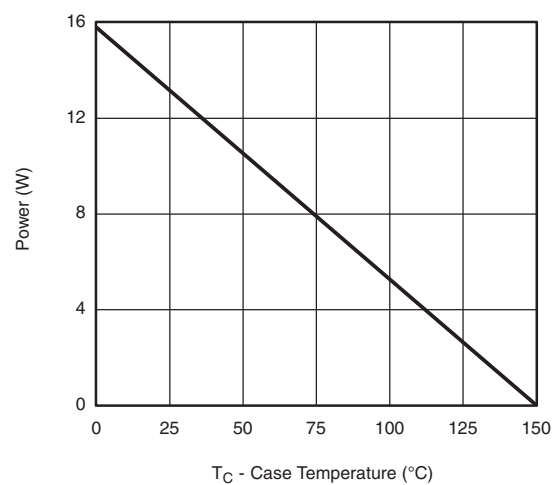
Safe Operating Area, Junction-to-Case



Current Derating**



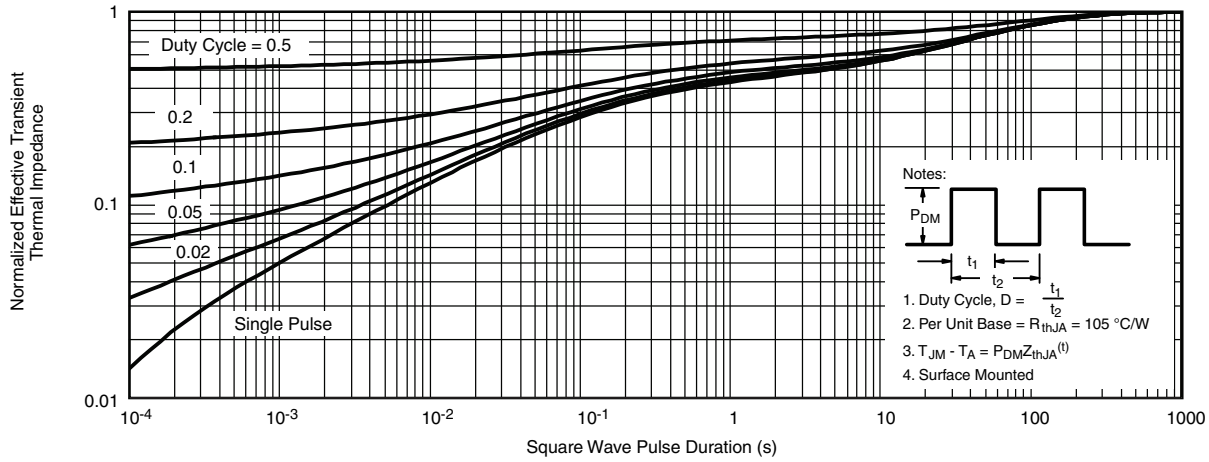
Power Junction-to-Ambient



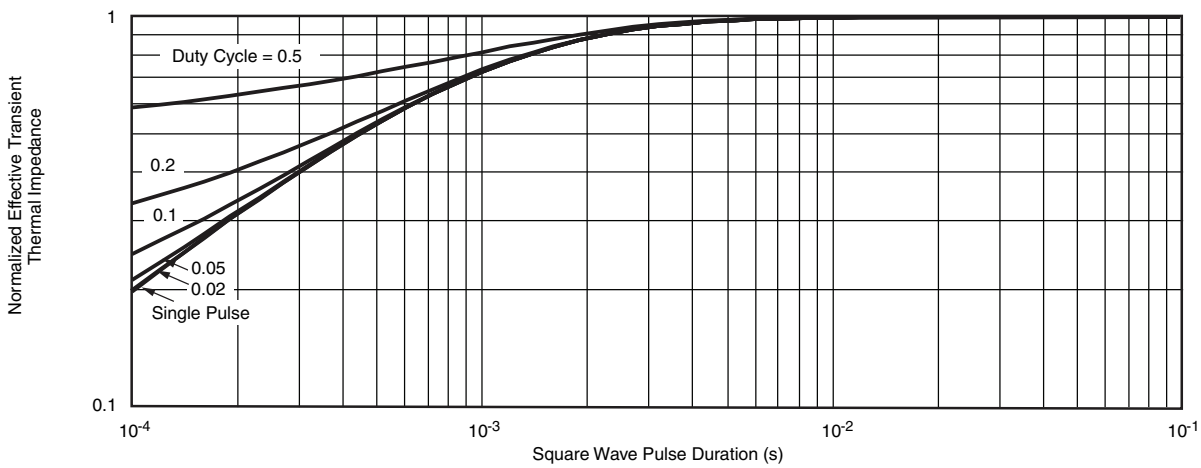
Power Junction-to-Case

** The power dissipation P_D is based on $T_{J(max.)} = 150^\circ\text{C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?63899.



PowerPAK® SC75-6L



BACKSIDE VIEW OF SINGLE

BACKSIDE VIEW OF DUAL



- Notes:
 1. All dimensions are in millimeters
 2. Package outline exclusive of mold flash and metal burr
 3. Package outline inclusive of plating

DIM	SINGLE PAD						DUAL PAD					
	MILLIMETERS			INCHES			MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max
A	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
b	0.18	0.25	0.33	0.007	0.010	0.013	0.18	0.25	0.33	0.007	0.010	0.013
C	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010
D	1.53	1.60	1.70	0.060	0.063	0.067	1.53	1.60	1.70	0.060	0.063	0.067
D1	0.57	0.67	0.77	0.022	0.026	0.030	0.34	0.44	0.54	0.013	0.017	0.021
D2	0.10	0.20	0.30	0.004	0.008	0.012						
E	1.53	1.60	1.70	0.060	0.063	0.067	1.53	1.60	1.70	0.060	0.063	0.067
E1	1.00	1.10	1.20	0.039	0.043	0.047	0.51	0.61	0.71	0.020	0.024	0.028
E2	0.20	0.25	0.30	0.008	0.010	0.012						
E3	0.32	0.37	0.42	0.013	0.015	0.017						
e	0.50 BSC			0.020 BSC			0.50 BSC			0.020 BSC		
K	0.180 TYP			0.007 TYP			0.245 TYP			0.010 TYP		
K1	0.275 TYP			0.011 TYP			0.320 TYP			0.013 TYP		
K2	0.200 TYP			0.008 TYP			0.200 BSC			0.008 TYP		
K3	0.255 TYP			0.010 TYP								
K4	0.300 TYP			0.012 TYP								
L	0.15	0.25	0.35	0.006	0.010	0.014	0.15	0.25	0.35	0.006	0.010	0.014
T							0.03	0.08	0.13	0.001	0.003	0.005

ECN: C-07431 – Rev. C, 06-Aug-07
 DWG: 5935

RECOMMENDED PAD LAYOUT FOR PowerPAK® SC75-6L Single



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